

Device Modeling Report

COMPONENTS: Zener Diode
PART NUMBER: DF3A6.8UFU
MANUFACTURER: TOSHIBA

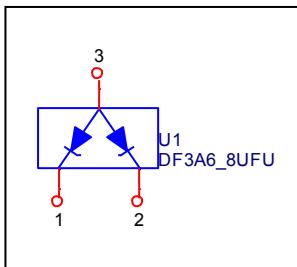


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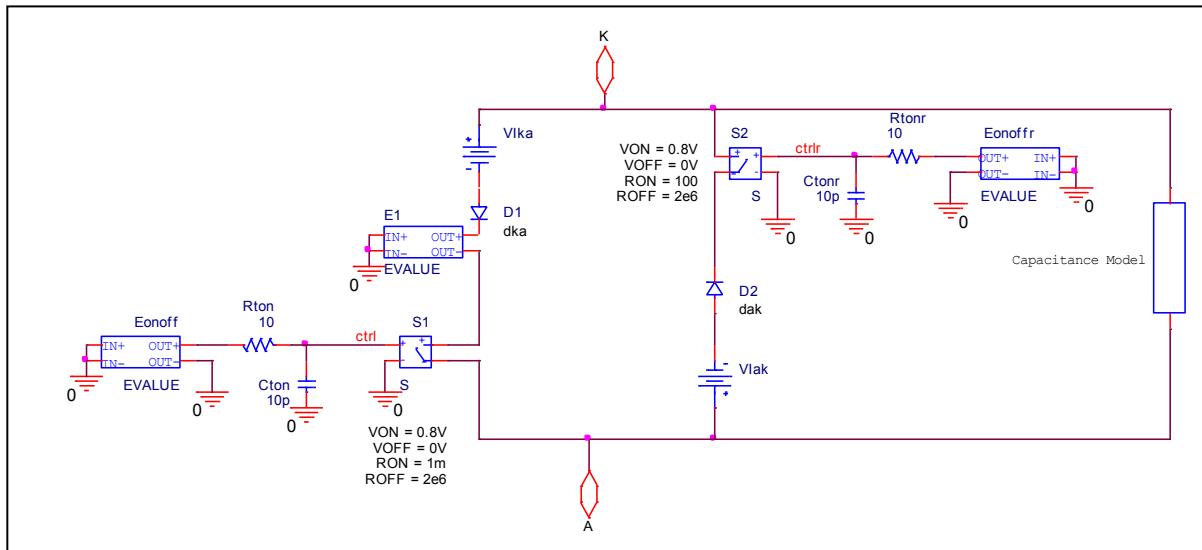
SPICE MODEL

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*$  
*PART NUMBER: DF3A6.8UFU  
*MANUFACTURER: TOSHIBA  
*REMARK: STANDARD MODEL  
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.SUBCKT DF3A6_8UFU 1 2 3  
X_U1 3 1 DF3A6  
X_U2 3 2 DF3A6  
.ENDS  
*$/  
.SUBCKT DF3A6 A K  
V_Vlak      A N60967 24.9Vdc  
D_D2        N60967 N60787 dak  
X_S2        CTRLR 0 K N60787 SCHEMATIC1_S2  
D_D3        A N605731 dc  
E_E1        N606431 N60703 VALUE  
{ IF(I(V_Vlka)<1u,I(V_Vlka),I(V_Vlka)*(-50)) }  
D_D4        K N605731 dc  
R_Rton      CTRL N61147 10  
R_Rtonr     CTRLR N60917 10  
C_Cton      CTRL 0 10p  
V_Vlka      K N606211 6.57Vdc  
C_Ctonr     CTRLR 0 10p  
D_D1        N606211 N606431 dka  
E_Eonoff    N61147 0 VALUE { IF(I(V_Vlka)>2.0uA,6.8,0) }  
E_Eonoffr   N60917 0 VALUE { IF(I(V_Vlak)>0.5uA,5,0) }  
X_S1        CTRL 0 N60703 A SCHEMATIC1_S1  
.model dak d (N=0.001 Cjo=0.03pF Rs=100m)  
.model dka d (N=0.001 Cjo=0.03pF Rs=100m)  
.model dc d (N=0.001 CJO=1.5954E-12 M=.10138 VJ=1.5008)  
.ENDS  
*$/  
.subckt SCHEMATIC1_S2 1 2 3 4  
S_S2        3 4 1 2 _S2  
RS_S2       1 2 1 G  
.MODEL      S2 VSWITCH Roff=2e6 Ron=100 Voff=0V Von=0.8V  
.ends SCHEMATIC1_S2  
*$/  
.subckt SCHEMATIC1_S1 1 2 3 4  
S_S1        3 4 1 2 _S1  
RS_S1       1 2 1 G  
.MODEL      S1 VSWITCH Roff=2e6 Ron=1m Voff=0V Von=0.8V  
.ends SCHEMATIC1_S1  
*$
```

Circuit Configuration



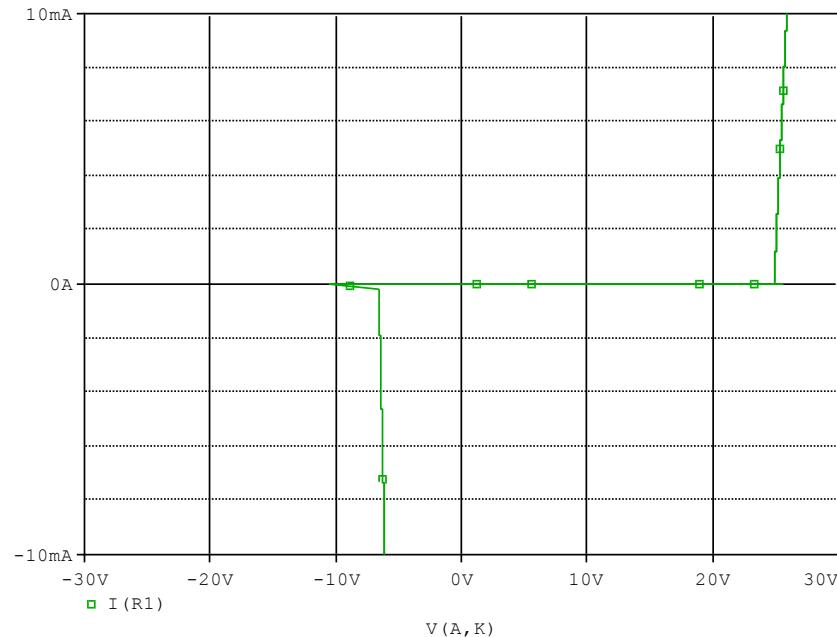
Equivalent circuit



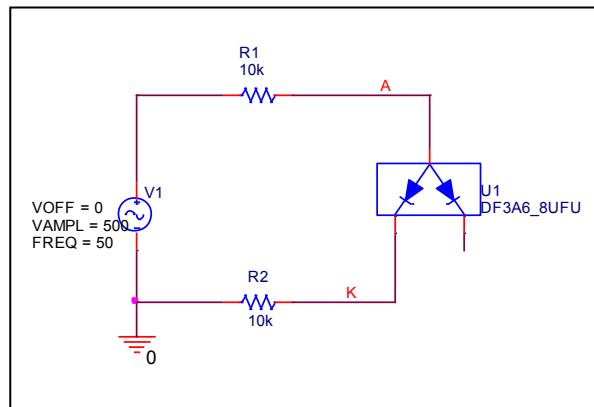
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
TT	Transit Time

Forward-Reverse Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



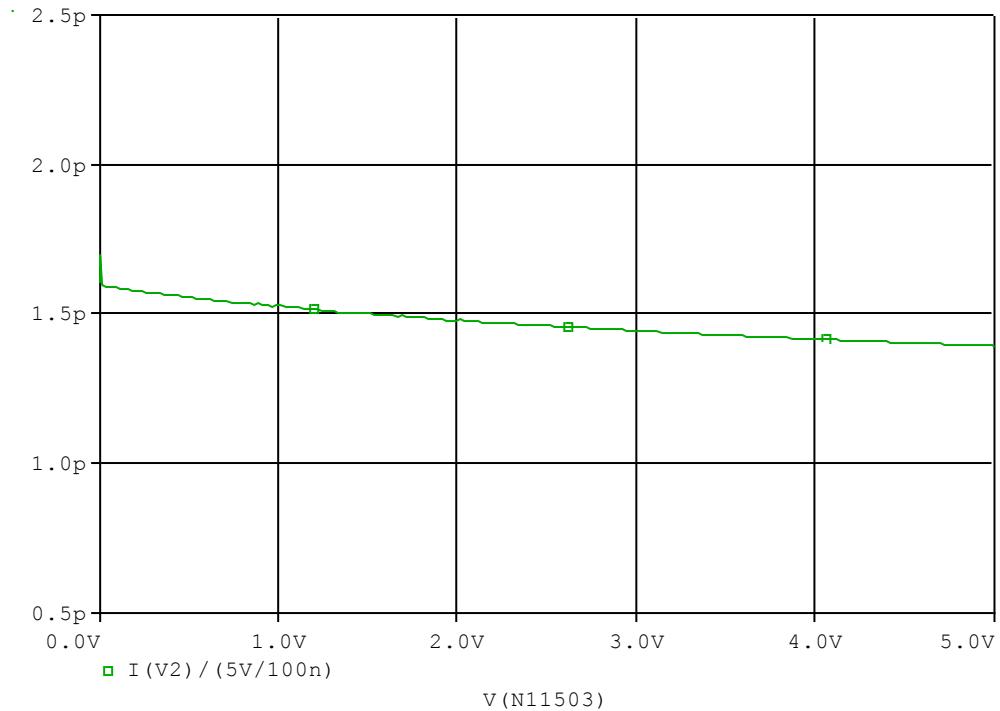
Compare Measurement vs. Simulation

Condition: $I_R=1\text{mA}$, $I_F=1\text{mA}$

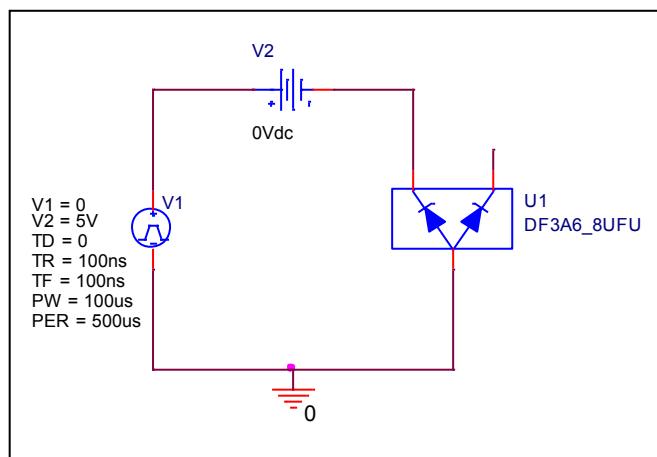
	Measurement	Simulation	%Error
V_R	V	6.800	6.521
V_F	V	25.000	25.001

Capacitance Characteristic

Circuit Simulation Result

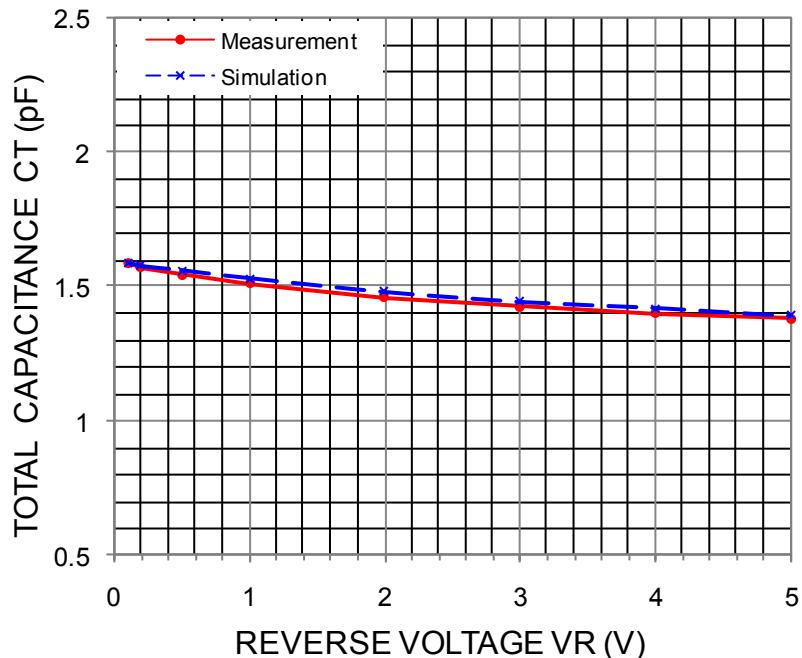


Evaluation Circuit



Comparison Graph

Circuit Simulation Result



Simulation Result

V_R (V)	C_T (pF)		%Error
	Measurement	Simulation	
0.1	1.590	1.587	-0.19
0.2	1.570	1.578	0.52
0.5	1.545	1.558	0.83
1	1.510	1.527	1.13
2	1.460	1.480	1.36
3	1.425	1.445	1.38
4	1.400	1.416	1.16
5	1.380	1.393	0.93